

MOSFET chip DMOST165

Description

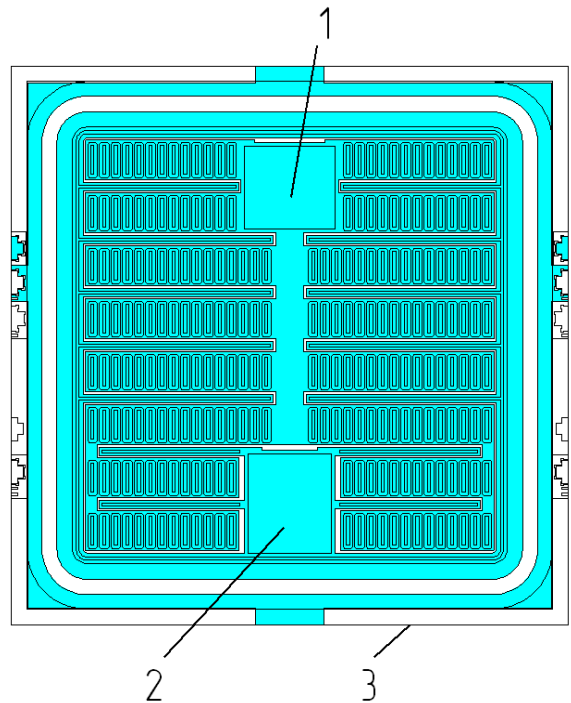
MOSFET chip with internal channel (normally-on)
DMOST165 is designed to be used in hybrid
microchips and packaged field-effect transistors.

Features

- Chip size – 1.44 x 1.44 mm
- Chip thickness – 0.36±0.02 mm
- Contact pads size:
Gate – 0.23 x 0.21 mm
Source – 0.22 x 0.25 mm
- Metallization: top – AlSi,
bottom – CrAu for bonding on
conductive adhesive

Absolute maximum ratings

Maximum Temperature	
Storage Temperature	- 60 °C to 100 °C
Operating Junction Temperature	- 45 °C to 85 °C
Maximum Voltage	
Drain-to-Source Voltage	230 V
Gate-to-Source Voltage	-25 V



- 1 - Gate
2 - Source
3 - Drain

Electrical characteristics (T = 25 °C)

Parameter	Symbol	Unit	Min.	Typ.	Max.	Conditions
Drain-to-Source ON-State Resistance	R_{DS}	Ohm			9.0	$V_{GS} = 0 \text{ V}$, $I_D = 150 \text{ mA}$
Drain Leakage Current	$I_{LEAK,D}$	μA			1.0	$V_{GS} = -4 \text{ V}$, $V_{DS} = 230 \text{ V}$
Gate Leakage Current	$I_{LEAK,G}$	μA			0.1	$V_{GS} = -25 \text{ V}$
LED Constant Forward Voltage (drain ⁻ , source ⁺)	V_{SD}	V			0.95	$V_{GS} = -4.5 \text{ V}$, $I_D = 150 \text{ mA}$
Drain Saturation Current	$V_{SAT,D}$	mA	100			$V_{GS} = -0.5 \text{ V}$, $V_{DS} = 5 \text{ V}$